

## CLAIMS

1. A fixed resistor network comprising an insulating substrate of rectangular shape in plan view, at least three film resistors formed on a top surface of the insulating substrate at a suitable pitch in a lengthwise direction of the insulating substrate, terminal electrodes formed for the film resistors on a lengthwise sidewall of the insulating substrate, and recesses provided between the terminal electrodes, a pitch between the terminal electrodes along the sidewall being at least 0.5 mm;  
wherein each recess has a width along the lengthwise sidewall which is from 0.44 to 0.48 times the pitch of the terminal electrodes, and terminal-electrode-forming areas between the recesses have a width along the lengthwise sidewall which is from 0.56 to 0.52 times the pitch of the terminal electrodes.
- 20 2. The fixed resistor network according to claim 1, wherein the terminal electrodes, recesses and terminal-electrode-forming areas are provided on both lengthwise sidewalls of the insulating substrate.
- 25 3. The fixed resistor network according to claim 1, wherein the terminal electrodes, recesses and terminal-electrode-forming areas are provided on at

least one of the two lengthwise sidewalls of the insulating substrate.

4. The fixed resistor network according to any one of  
5 claims 1 to 3, wherein the pitch between the terminal electrodes is 0.5 mm or approximately 0.5 mm.

5. The fixed resistor network according to any one of claims 1 to 3, wherein the insulating substrate has a  
10 length L of approximately 2.0 mm and a width W of approximately 1.0 mm.

6. The fixed resistor network according to any one of claims 1 to 3, wherein the insulating substrate has a  
15 length L of approximately 3.8 mm and a width W of approximately 1.6 mm.

7. A fixed resistor network comprising an insulating substrate of rectangular shape in plan view, at least  
20 three film resistors formed on a top surface of the insulating substrate at a suitable pitch in a lengthwise direction of the insulating substrate, terminal electrodes formed for the film resistors on a lengthwise sidewall of the insulating substrate, and  
25 recesses provided between the terminal electrodes, a pitch between the terminal electrodes along the sidewall being not more than 0.4 mm;

wherein each recess has a width along the lengthwise sidewall of the insulating substrate which is from 0.525 to 0.625 times the pitch of the terminal electrodes, and terminal-electrode-forming areas 5 between the recesses have a width along the lengthwise sidewall of the insulating substrate which is from 0.475 to 0.375 times the pitch of the terminal electrodes.

10 8. The fixed resistor network according to claim 7, wherein the recesses have a depth from the lengthwise sidewall of the insulating substrate which is from 0.512 to 0.645 times the width of the terminal-electrode-forming areas.

15

9. The fixed resistor network according to claim 7, wherein the recesses have a width along the lengthwise sidewall of the insulating substrate of 0.21 to 0.25 mm and the terminal-electrode-forming areas between 20 the recesses have a width along the lengthwise sidewall of the insulating substrate of 0.19 to 0.15 mm.

25 10. The fixed resistor network according to claim 8, wherein the recesses have a depth of 0.077 to 0.12 mm from the lengthwise sidewall of the insulating substrate.